2SA1535, 2SA1535A

Silicon PNP epitaxial planar type

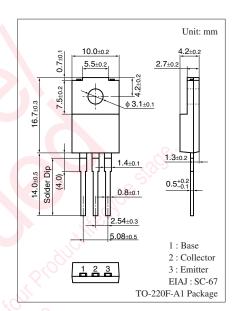
For low-frequency driver and high power amplification Complementary to 2SC3944, 2SC3944A

Features

- Excellent collector current I_C characteristics of forward current transfer ratio h_{FE}
- High transition frequency f_T
- A complementary pair with 2SC3944 and 2SC3944A, is optimum for the driver-stage of a 60 W to 100 W output amplifier

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SA1535	V_{CBO}	-150	V
(Emitter open)	2SA1535A		-180	
Collector-emitter voltage	2SA1535	V _{CEO}	-150	V
(Base open)	2SA1535A		-180	
Emitter-base voltage (Coll	V _{EBO}	-5	V	
Collector current	I_{C}	-1	A	
Peak collector current	I_{CP}	-1.5	A	
Collector power dissipation	$T_C = 25^{\circ}C$	P _C	15	S W
			2	
Junction temperature		T_{j}	150	°C
Storage temperature		T _{stg}	-55 to +150	°C



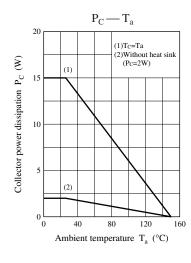
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

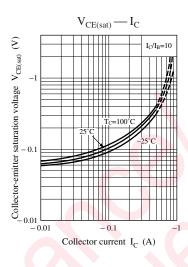
Parameter	20:00	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	ollector-emitter voltage 2SA1535		V_{CEO} $I_{C} = -100 \mu\text{A}, I_{B} = 0$				V
(Base open)	2SA1535A		$I_{\rm C} = -100 \mu\text{A}, I_{\rm B} = 0$	-180			
Emitter-base voltage (Collector open)		V _{EBO}	$I_E = -10 \mu A, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	2SA1535	I_{CBO}	$V_{CB} = -150 \text{ V}, I_E = 0$			-10	μА
Forward current transfer ratio		h _{FE1} *	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	65	160	330	_
		h _{FE2}	$V_{CE} = -5 \text{ V}, I_{C} = -500 \text{ mA}$	50	100		
Collector-emitter saturation	voltage	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.5	-2.0	V
Base-emitter saturation vol	tage	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		-1.0	-2.0	V
Transition frequency		f_T	$V_{CE} = -10 \text{ V}, I_{C} = -50 \text{ mA}, f = 10 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)		C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		30	50	pF

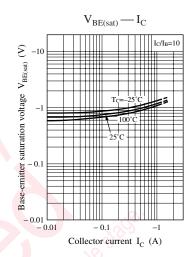
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

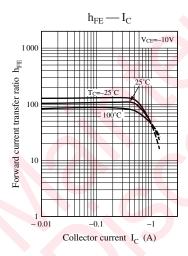
2. *: Rank classification

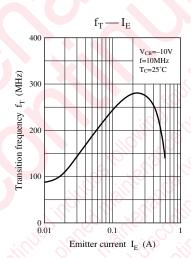
Rank	Р	Q	R	S
h _{FE1}	65 to 110	90 to 155	130 to 220	185 to 330

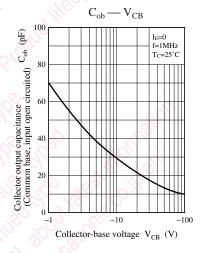












Safe operation area Single pulse TC=25°C Lep DC Lelims -0.001 -0.001 -100 Collector-emitter voltage V_{CE} (V)

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